

AMENDMENTS

IN THE SPECIFICATION

- 1) page 4, lines 19 and 20, replace this paragraph with:

A1
Figs. 1a through 1e show the current Prior Art one-step cleaning process as applied to a (photolithography) mask.

- NE
2) page 8, line 23, please remove ""

- 3) page 10, lines 3 and 4, replace the paragraph:

Fig. 1 shows the sequence of events during the original, Prior Art one-step rf power-down mode.

with the following:

A2
Figs. 1a through 1e show the sequence of events during the original, Prior Art one-step rf power-down mode, as follows:

Figs. 1a and 1b show conventional conditions referring to a first (Fig. 1a) and a second (Fig. 1b) execution of the same process of cleaning the dry-etch chamber under identical operating conditions of the cleaning operation.

Fig. 1c shows the condition within the dry-etch chamber between the Fig. 1a and Fig. 1b cycle of the dry-etch process.

*A2
Contd.*
Fig. 1d shows the repeat of the conventional dry-etch cleaning process.

Fig. 1e shows the distribution of the wall polymer or other residual reaction product molecules after Fig. 1b of the dry-etch cleaning process has been completed and after the internal conditions of the chamber have stabilized.

4) page 10, line 6 and 7, replace the paragraph:

Fig. 2 shows the sequence of events during the multi-step rf power-down mode of the invention.

with the following:

AB
Figs. 2a through 2e show the sequence of events during the multi-step rf power-down mode of the invention, as follows:

Fig. 2a shows the dry-clean chamber with elements that are contained within and used by the dry-clean chamber. Polymer depositions are also highlighted in Fig. 2a.

Fig. 2b shows the wall polymer or other residual reaction product molecules being distributed throughout the chamber after the rf coil has been activated and the RIE etch has been started. Fig. 2b represents the first step of the power-down sequence of the dry-etch process.

Fig. 2c shows the condition within the dry-etch chamber during execution of dry-etch power-down step 2 within the sequence of six steps of the present invention.

Fig. 2d shows the subsequent steps 4, 5 and 6 of the dry-etch power-down sequence of the present invention.

Fig. 2e shows the final condition within the dry-etch chamber after applying the six step power-down sequence of the present invention.

5) page 10, lines 9, 10 and 11, replace the paragraph:

Fig. 3 shows a graphic depiction of the particle count for both the original Prior Art one step rf power-down mode and the multi-step rf power-down mode of the invention.

with the following:

Figs. 3a and 3b show a graphic depiction of the particle count for both the original Prior Art one step rf power-down mode and the multi-step rf power-down mode of the invention, as follows:

Fig. 3a shows the Prior Art particle count as a function of time with varying levels of applied rf power.

Fig. 3b shows the particle count obtained under the present invention.

6) page 10, lines 13 and 14, replace the paragraph:

Fig. 4 shows a graph further illustrating the results obtained using the power-down procedure of the invention.
with the following:

Figs. 4a and 4b show a graph further illustrating the results obtained using the power-down procedure of the invention, as follows: